# ST 2N5086 / 2N5087

#### **PNP Silicon Epitaxial Planar Transistor**

for switching and AF amplifier applications.

The transistor is subdivided into one group according to it DC current gain. As complementary type the NPN transistor ST 2N5088 and ST 2N5089 are recommended.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector

TO-92 Plastic Package Weight approx. 0.19g

Denenation	O maked	Malaa	1.1	
Parameter	Symbol	Value	Unit	
Collector Base Voltage	-V <sub>CBO</sub>	50	V	
Collector Emitter Voltage	-V <sub>CEO</sub>	50	V	
Emitter Base Voltage	-V <sub>EBO</sub>	3	V	
Collector Current	-I <sub>C</sub>	50	mA	
Power Dissipation	P <sub>tot</sub>	500	mW	
Junction Temperature	Tj	150	°C	
Storage Temperature Range	Ts	-55 to +150	°C	

#### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)







#### Characteristics at T<sub>amb</sub> = 25 °C

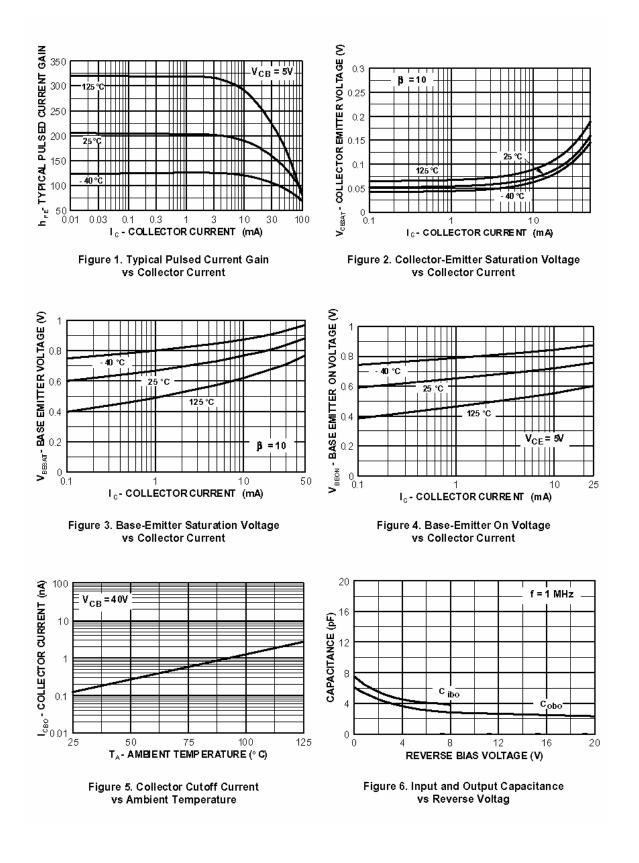
Parameter		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain at -V <sub>CE</sub> =5V, -I <sub>C</sub> =0.1mA	ST 2N5086	h <sub>FE</sub>	150	-	500	-
at -V <sub>CE</sub> =5V, -I <sub>C</sub> = 1mA	ST 2N5087 ST 2N5086	h <sub>FE</sub> h <sub>FE</sub>	200 150	-	800 -	-
at -V <sub>CE</sub> =5V, -I <sub>C</sub> = 10mA	ST 2N5087 ST 2N5086 ST 2N5087	h <sub>FE</sub> h <sub>FE</sub> h <sub>FE</sub>	200 150 200			
Collector Base Breakdown Voltage at -I <sub>C</sub> =100µA	9	-V <sub>(BR)CBO</sub>	50	-	-	V
Collector Emitter Breakdown Volta at -I <sub>C</sub> =1mA	ge	-V <sub>(BR)CEO</sub>	50	-	-	V
Emitter Base Breakdown Voltage at -I <sub>E</sub> =10µA		-V <sub>(BR)EBO</sub>	3	-	-	V
Collector Cutoff Current at -V <sub>CB</sub> =35V		-I <sub>CBO</sub>	-	-	0.05	μΑ
Emitter Cutoff Current at -V <sub>EB</sub> =3V		-I <sub>EBO</sub>	-	-	0.05	μΑ
Collector Saturation Voltage at -I <sub>C</sub> =10mA, -I <sub>B</sub> =1mA		-V <sub>CE(sat)</sub>	-	-	0.3	V
Base Emitter Voltage at -V <sub>CE</sub> =5V, -I <sub>C</sub> =1mA		$-V_{BE(on)}$	-	-	0.85	V
Gain Bandwidth Product at -V <sub>CE</sub> =5V, -I <sub>C</sub> =0.5mA		f <sub>T</sub>	40	180	-	MHz
Output Capacitance at -V <sub>CB</sub> =10V, f=1MHz		C <sub>OB</sub>	-	2.8	-	pF
Noise Figure at -V <sub>CE</sub> =6V, -I <sub>C</sub> =0.3mA, f=100Hz	, R <sub>s</sub> =10KΩ	NF	-	-	3	dB





Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

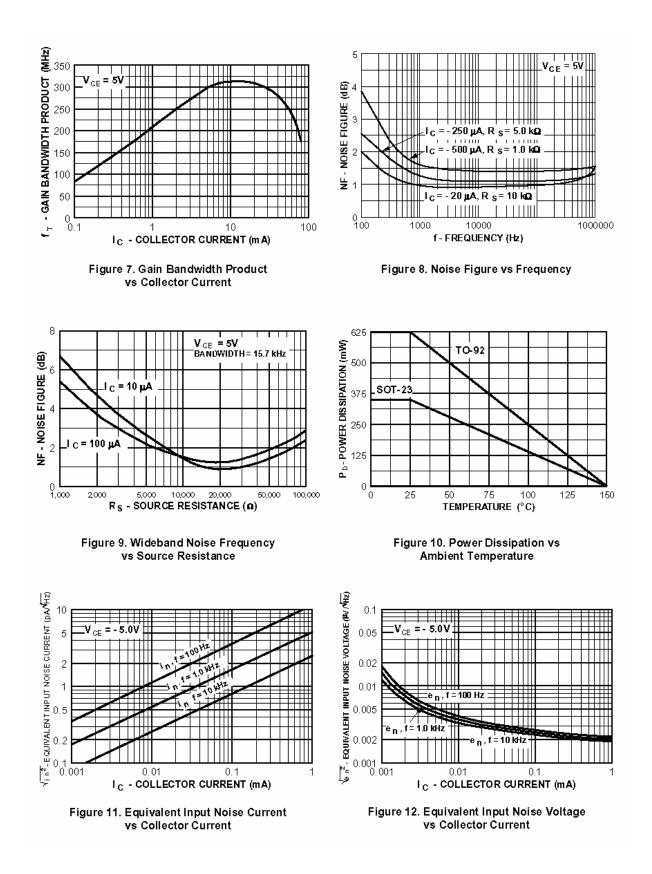






SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724) 
NOODY
Image: Construction of the second second

## ST 2N5086 / 2N5087



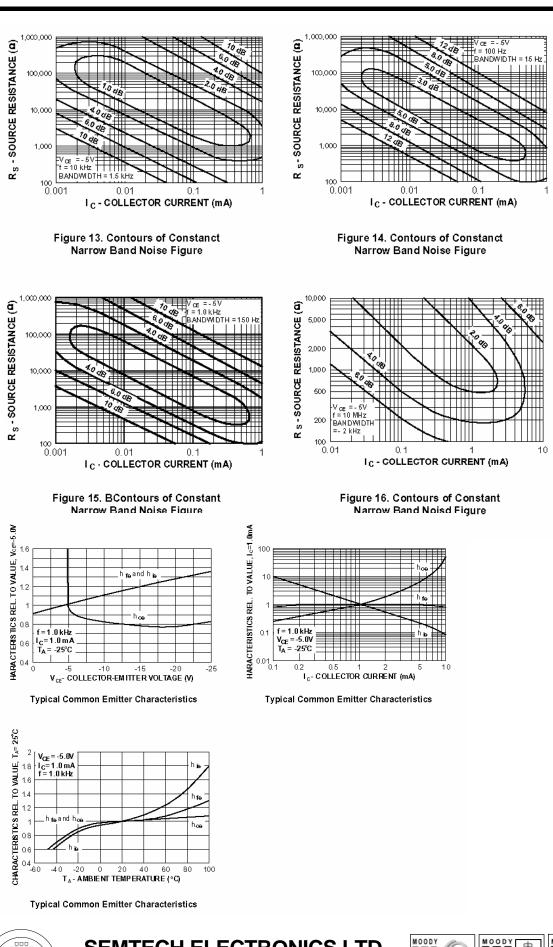


SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



### ST 2N5086 / 2N5087





SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company

listed on the Hong Kong Stock Exchange, Stock Code: 724)

